

TLP 759(D4)

Types : TLP759, TLP759F



Ex. : TLP759 (D4-O) D4 : VDE0884 option
O : CTR rank

Ex. TLP759 (D4-O) \rightarrow TLP759

DESCRIPTION		SYMBOL	RATING	UNIT
Application Classification (DIN VDE0109 / 12.83, Table 1) for rated mains voltage $\leq 300 \text{ V}_{\text{RMS}}$ for rated mains voltage $\leq 600 \text{ V}_{\text{RMS}}$			I-IV I-III	—
Climatic Classification (DIN IEC68 Teil 1 / 09.80)			55 / 100 / 21	—
Pollution Degree (DIN VDE0109 / 12.83)			2	—
Maximum Operating Insulation Voltage	TLPxxx	V_{IORM}	890	V_{pk}
	TLPxxxF		1140	
Input to output Test Voltage, Method A $V_{\text{pr}} = 1.5 \times V_{\text{IORM}}$, 100% Production Test $t_{\text{p}} = 60\text{s}$, Partial Discharge $< 5\text{pC}$	TLPxxx	V_{pr}	1335	V_{pk}
	TLPxxxF		1710	
Input to output Test Voltage, Method B $V_{\text{pr}} = 1.875 \times V_{\text{IORM}}$, 100% Production Test $t_{\text{p}} = 1\text{s}$, Partial Discharge $< 5\text{pC}$	TLPxxx	V_{pr}	1670	V_{pk}
	TLPxxxF		2140	
Highest Permissible Overvoltage (Transient Overvoltage, $t_{\text{pr}} = 10\text{s}$)		V_{TR}	6000	V_{pk}
Safety Limiting Values (Max. permissible ratings in case of fault, also refer to thermal derating curve) Current (Input current I_{F} , $\text{Psi} = 0$) Power (Output or Total Power Dissipation) Temperature		Isi Psi Tsi	300 500 150	mA mW °C
Insulation Resistance at Tsi, $V_{\text{IO}} = 500\text{V}$		Rsi	$\geq 10^9$	Ω

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INSULATION RELATED SPECIFICATIONS

			 7.62mm pitch TLP759	 10.16mm pitch TLP759F
Minimum Creepage Distance (*)	Cr		6.4mm	8.0mm
Minimum Clearance (*)	Cl		6.4mm	8.0mm
Minimum Insulation Thickness	ti		0.4mm	
Comperative Tracking Index (DIN IEC112 / VDE0303, Part 1)	CTI		175 (VDE0109 / 12.83 Group III a)	

(*) in accordance with DIN VDE0109 / 12.83, Table 2, & 4

1. If a printed circuit is incorporated, the creepage distance and clearance may be reduced below this value (e. g. at a standard distance between soldering eye centres of 7.5mm). If this is not permissible, the user shall take suitable measures.
2. This photocoupler is suitable for 'safe electrical isolation' only within the safety limit data. Maintenance of the safety data shall be ensured by means of protective circuits.

VDE Test sign : Marking on product
for VDE0884



Marking on packing
for VDE0884



Marking Example :

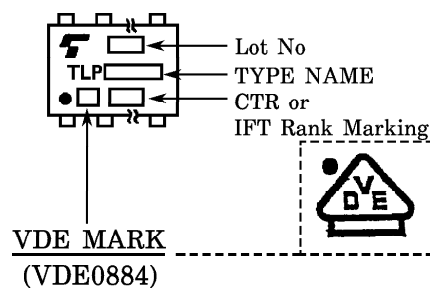


Figure 1 Partial discharge measurement procedure according to VDE0884
Destructive test for qualification and sampling tests.

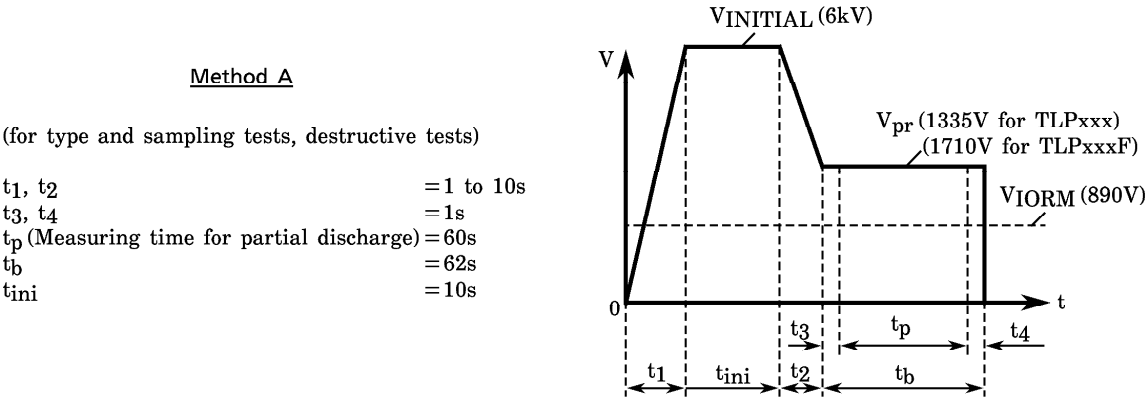


Figure 2 Partial discharge measurement procedure according to VDE0884
Non-destructive test for 100% inspection.

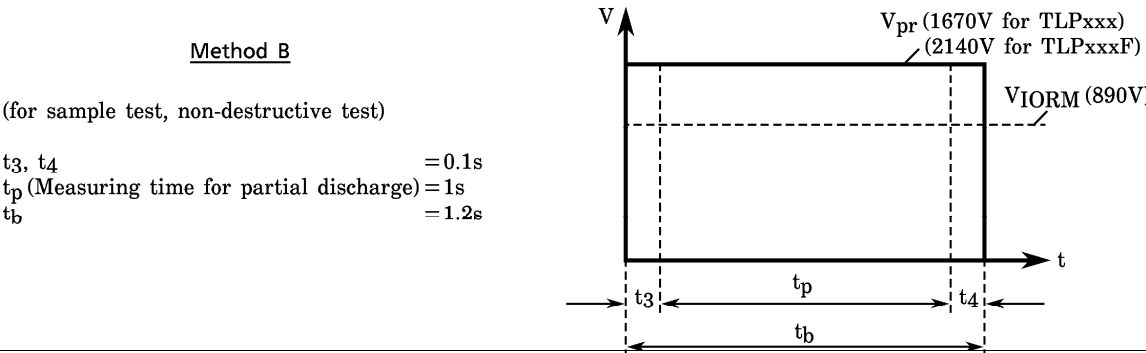


Figure 3 Dependency of maximum safety ratings on ambient temperature

